



3.3V CMOS OCTAL BUS TRANSCEIVER WITH 3-STATE OUTPUTS AND 5 VOLT TOLERANT I/O

IDT74LVCR245A ADVANCE INFORMATION

FEATURES:

- 0.5 MICRON CMOS Technology
- ESD > 2000V per MIL-STD-883, Method 3015;
> 200V using machine model (C = 200pF, R = 0)
- 1.27mm pitch SOIC, 0.65mm pitch SSOP,
0.635mm pitch QSOP, 0.65mm pitch TSSOP packages
- Extended commercial range of -40°C to +85°C
- Vcc = 3.3V ±0.3V, Normal Range
- Vcc = 2.3V to 3.6V, Extended Range
- CMOS power levels (0.4μW typ. static)
- Rail-to-Rail output swing for increased noise margin
- All inputs, outputs and I/O are 5 Volt tolerant
- Supports hot insertion

Drive Features for LVCR245A:

- Balanced Output Drivers: ±12mA
- Low Switching Noise

DESCRIPTION:

The LVCR245A octal bus transceiver is built using advanced dual metal CMOS technology. This device is designed for asynchronous communication between data buses. The device transmits data from the A bus to the B bus or from the B bus to the A bus, depending on the logic level at the direction-control (DIR) input. The output-enable (\overline{OE}) input can be used to disable the device so the buses are effectively isolated.

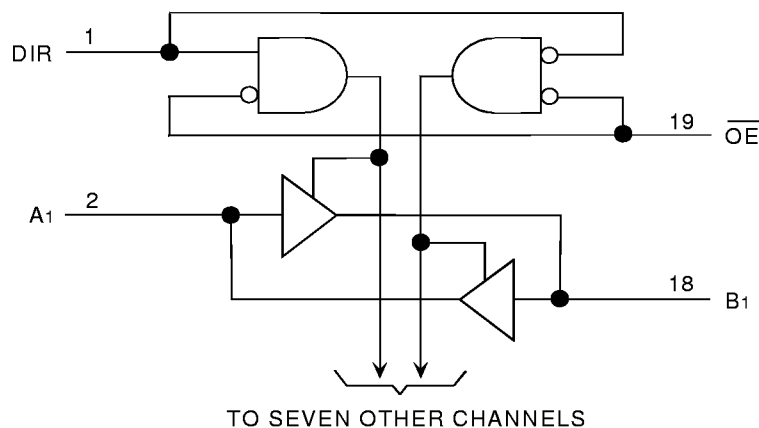
The LVCR245A has series resistors in the output structure which will significantly reduce line noise when used with light loads. The driver has been designed to drive ±12mA at the designated threshold.

Inputs can be driven from either 3.3V or 5V devices. This feature allows the use of this device as a translator in a mixed 3.3V/5V environment.

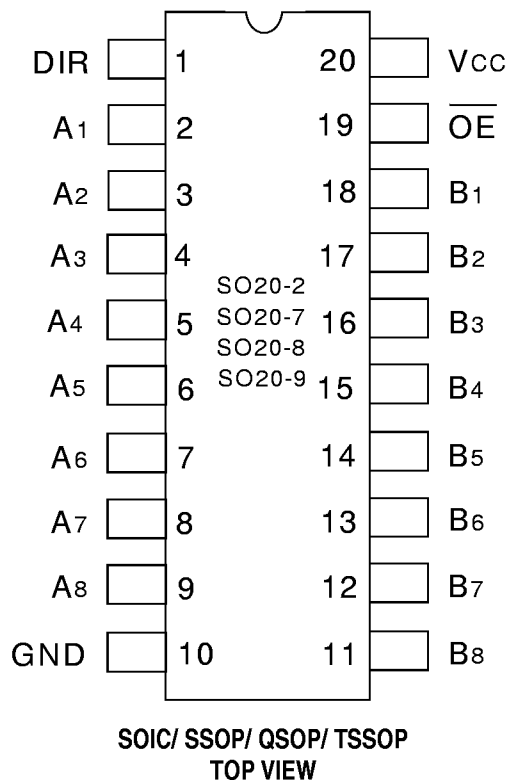
APPLICATIONS:

- 5V and 3.3V mixed voltage systems
- Data communication and telecommunication systems

Functional Block Diagram



PIN CONFIGURATION



ABSOLUTE MAXIMUM RATINGS (1)

Symbol	Description	Max.	Unit
V _{TERM} (2)	Terminal Voltage with Respect to GND	-0.5 to +6.5	V
V _{TERM} (3)	Terminal Voltage with Respect to GND	-0.5 to +6.5	V
T _{STG}	Storage Temperature	-65 to +150	°C
I _{OUT}	DC Output Current	-50 to +50	mA
I _{IK} I _{OK}	Continuous Clamp Current, V _I < 0 or V _O < 0	-50	mA
I _{CC} I _{SS}	Continuous Current through each V _{CC} or GND	±100	mA

NOTES:

- Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.
- V_{CC} terminals.
- All terminals except V_{CC}.

CAPACITANCE (T_A = +25°C, f = 1.0MHz)

Symbol	Parameter(1)	Conditions	Typ.	Max.	Unit
C _{IN}	Input Capacitance	V _{IN} = 0V	4.5	6	pF
C _{OUT}	Output Capacitance	V _{OUT} = 0V	5.5	8	pF
C _{I/O}	I/O Port Capacitance	V _{IN} = 0V	6.5	8	pF

NOTE:

- As applicable to the device type.

PIN DESCRIPTION

Pin Names	Description
\overline{OE}	Output-enable Input (Active LOW)
A _x , B _x	Data Inputs or 3-State Outputs
DIR	Direction-control Input

FUNCTION TABLE (1)

Inputs		Outputs
\overline{OE}	DIR	
L	L	B data to A bus
L	H	A data to B bus
H	X	Isolation

NOTE:

- H = HIGH Voltage Level
L = LOW Voltage Level
X = Don't Care

DC ELECTRICAL CHARACTERISTICS OVER OPERATING RANGE

Following Conditions Apply Unless Otherwise Specified:

Operating Condition: TA = -40°C To +85°C

Symbol	Parameter	Test Conditions		Min.	Typ. ⁽¹⁾	Max.	Unit
V _{IH}	Input HIGH Voltage Level	V _{CC} = 2.3V to 2.7V		1.7	—	—	V
		V _{CC} = 2.7V to 3.6V		2	—	—	
V _{IL}	Input LOW Voltage Level	V _{CC} = 2.3V to 2.7V		—	—	0.7	V
		V _{CC} = 2.7V to 3.6V		—	—	0.8	
I _{IH} I _{IL}	Input Leakage Current	V _{CC} = 3.6V	V _I = 0 to 5.5V	—	—	±5	μA
I _{OZH} I _{OZL}	High Impedance Output Current (3-State Output pins)	V _{CC} = 3.6V	V _O = 0 to 5.5V	—	—	±10	μA
I _{OFF}	Input/Output Power Off Leakage	V _{CC} = 0V, V _{IN} or V _O ≤ 5.5V		—	—	±50	μA
V _{IK}	Clamp Diode Voltage	V _{CC} = 2.3V, I _{IN} = -18mA		—	-0.7	-1.2	V
V _H	Input Hysteresis	V _{CC} = 3.3V		—	100	—	mV
I _{CC1} I _{CC2} I _{CC3}	Quiescent Power Supply Current	V _{CC} = 3.6V	V _{IN} = GND or V _{CC}	—	—	10	μA
			3.6 ≤ V _{IN} ≤ 5.5V ⁽²⁾	—	—	10	
ΔI _{CC}	Quiescent Power Supply Current Variation	One input at V _{CC} - 0.6V, other inputs at V _{CC} or GND		—	—	500	μA

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NOTES:

- Typical values are at V_{CC} = 3.3V, +25°C ambient.
- This applies in the disabled state only.

OUTPUT DRIVE CHARACTERISTICS

Symbol	Parameter	Test Conditions ⁽¹⁾		Min.	Max.	Unit
V _{OH}	Output HIGH Voltage	V _{CC} = 2.3V to 3.6V	I _{OH} = -0.1mA	V _{CC} - 0.2	—	V
		V _{CC} = 2.3V	I _{OH} = -4mA	1.9	—	
			I _{OH} = -6mA	1.7	—	
		V _{CC} = 2.7V	I _{OH} = -4mA	2.2	—	
			I _{OH} = -8mA	2	—	
		V _{CC} = 3.0V	I _{OH} = -6mA	2.4	—	
I _{OH} = -12mA	2		—			
V _{OL}	Output LOW Voltage	V _{CC} = 2.3V to 3.6V	I _{OL} = 0.1mA	—	0.2	V
		V _{CC} = 2.3V	I _{OL} = 4mA	—	0.4	
			I _{OL} = 6mA	—	0.55	
		V _{CC} = 2.7V	I _{OL} = 4mA	—	0.4	
			I _{OL} = 8mA	—	0.6	
		V _{CC} = 3.0V	I _{OL} = 6mA	—	0.55	
	I _{OL} = 12mA	—	0.8			

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NOTE:

- V_{IH} and V_{IL} must be within the min. or max. range shown in the DC ELECTRICAL CHARACTERISTICS OVER OPERATING RANGE table for the appropriate V_{CC} range. TA = -40°C to +85°C.

OPERATING CHARACTERISTICS, $V_{CC} = 3.3V \pm 0.3V$, $T_A = 25^\circ C$

Symbol	Parameter	Test Conditions	Typical	Unit
CPD	Power dissipation capacitance per transceiver Outputs enabled	$C_L = 0pF$, $f = 10MHz$	48	pF
CPD	Power dissipation capacitance per transceiver Outputs disabled		4	pF

SWITCHING CHARACTERISTICS (1)

Symbol	Parameter	$V_{CC} = 2.5V \pm 0.2V$		$V_{CC} = 2.7V$		$V_{CC} = 3.3V \pm 0.3V$		Unit
		Min.	Max.	Min.	Max.	Min.	Max.	
t_{PLH}	Propagation Delay	—	—	—	7.3	1.5	6.3	ns
t_{PHL}	Ax or Bx to Bx or Ax	—	—	—	7.3	1.5	6.3	ns
t_{PZH}	Output Enable Time	—	—	—	9.5	1.5	8.2	ns
t_{PZL}	\overline{OE} or DIR to Ax or Bx	—	—	—	9.5	1.5	8.2	ns
t_{PHZ}	Output Disable Time	—	—	—	8.5	1.7	7.8	ns
t_{PLZ}	\overline{OE} or DIR to Ax or Bx	—	—	—	8.5	1.7	7.8	ns
$t_{sk(0)}$	Output Skew(2)	—	—	—	—	—	1	ns

NOTES:

1. See test circuits and waveforms. $T_A = -40^\circ C$ to $+85^\circ C$.
2. Skew between any two outputs of the same package and switching in the same direction.

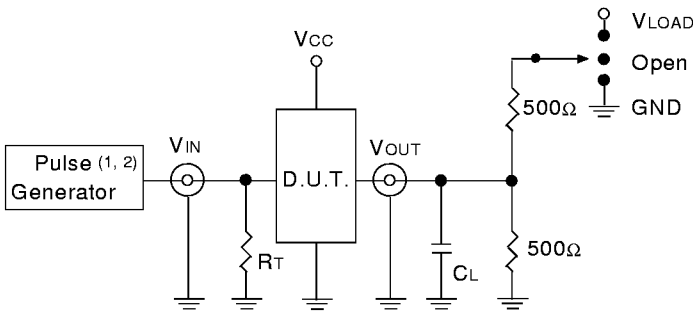
TEST CIRCUITS AND WAVEFORMS

TEST CONDITIONS

Symbol	Vcc(1)= 3.3V ±0.3V	Vcc(1)= 2.7V	Vcc(2)= 2.5V ±0.2V	Unit
V _{LOAD}	6	6	2 x V _{cc}	V
V _{IH}	2.7	2.7	V _{cc}	V
V _T	1.5	1.5	V _{cc} / 2	V
V _{LZ}	300	300	150	mV
V _{HZ}	300	300	150	mV
C _L	50	50	30	pF

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TEST CIRCUITS FOR ALL OUTPUTS



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DEFINITIONS:

C_L = Load capacitance: includes jig and probe capacitance.
 R_T = Termination resistance: should be equal to Z_{OUT} of the Pulse Generator.

NOTES:

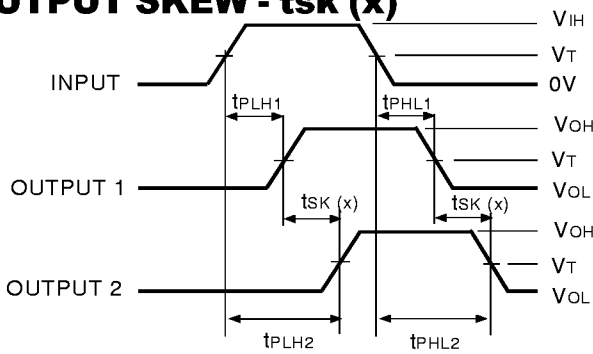
1. Pulse Generator for All Pulses: Rate ≤ 10MHz; t_F ≤ 2.5ns; t_R ≤ 2.5ns.
2. Pulse Generator for All Pulses: Rate ≤ 10MHz; t_F ≤ 2ns; t_R ≤ 2ns.

SWITCH POSITION

Test	Switch
Open Drain Disable Low Enable Low	V _{LOAD}
Disable High Enable High	GND
All Other tests	Open

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OUTPUT SKEW - t_{SK}(x)



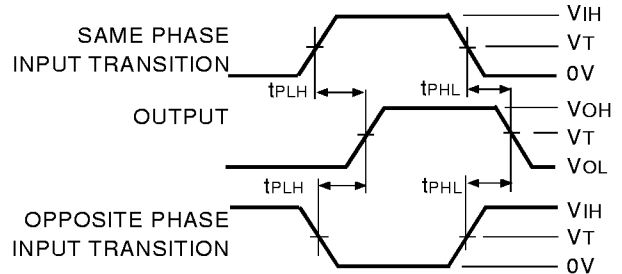
$$t_{SK}(x) = |t_{PLH2} - t_{PLH1}| \text{ or } |t_{PHL2} - t_{PHL1}|$$

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NOTES:

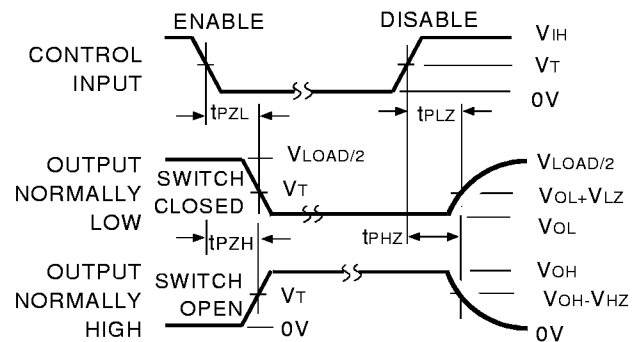
1. For t_{SK}(o) OUTPUT1 and OUTPUT2 are any two outputs.
2. For t_{SK}(b) OUTPUT1 and OUTPUT2 are in the same bank.

PROPAGATION DELAY



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ENABLE AND DISABLE TIMES

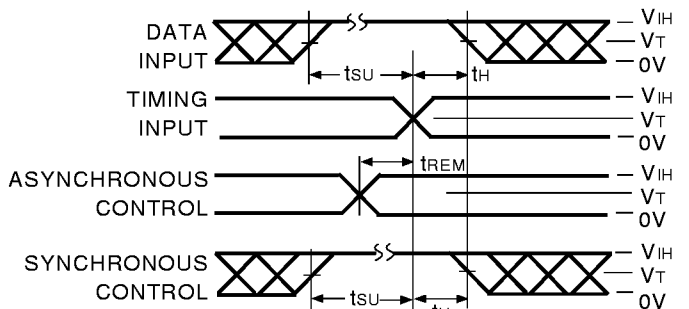


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NOTE:

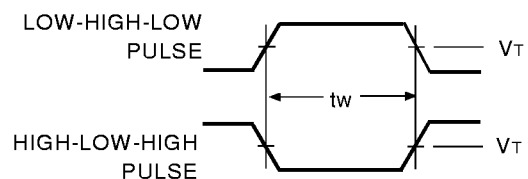
1. Diagram shown for input Control Enable-LOW and input Control Disable-HIGH.

SET-UP, HOLD, AND RELEASE TIMES



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PULSE WIDTH



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ORDERING INFORMATION

IDT	XX	LVC	X	XXXX	XX	
Temp. Range	Bus-Hold	Device Type	Package			
						SO Small Outline IC (gull wing) (SO20-2)
						PY Shrink Small Outline Package (SO20-7)
						Q Quarter Size Small Outline Package (SO20-8)
						PG Thin Shrink Small Outline Package (SO20-9)
						R245A Octal Bus Transceiver with 3-State Outputs, ±12mA
						Blank No Bus-hold
						74 -40 °C to +85 °C



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